

Index

A

Absorption coefficient, 459, 472
 Active centers, interfacial phenomenon, 326
 Activity fields, 256
 Aluminum gate capacitors, 263
 Amorphous silicon, 222
 Annealing
 At high temperatures, 315
 At low temperatures, 363
 Arsenic diffusion in silicon, 294
 Arsenic implant, 290
 ASTM Committee F-1 on Electronics, 538
 Auger electron spectroscopic technique, 278, 284
 Autodoping, 151, 157, 162, 168, 176
 Automatic wafer inspection, 492
 Axial distribution, 7, 28, 41, 370

B

Backside damage, 350, 390
 Ion implanted, 350
 Mechanical, 350
 Barrel reactor, 148, 175
 Bipolar technology, 151, 167, 174, 238
 Bit line coupling, 193
 Bit sense lines, 191
 Boltzmann-Matano analysis, 293
 Bulk defects in silicon, 332
 Buried layer, 152, 158, 174, 411

C

Capacitance transient measurements, 241
 Carbon in silicon, 8, 39, 317, 362, 445, 455
 Characterization techniques
 Cumulative frequency plots, 432
 Equivalence contours, 428
 For large-diameter wafers, 422, 446
 Halftone maps, 425
 Ion implant uniformity, 422, 454
 Resistivity mapping, 423
 Symbolic maps, 425
 Three-dimensional maps, 432
 Vector maps, 431
 Charge-couple device (CCD) imager, 311
 Charges in oxide, 242
 Chemical vapor deposition (CVD), 147, 151, 257
 Chlorine distributions in oxide, 252
 Chlorosiloxane film, 248, 253
 Constant field device scaling, 230
 Contamination during high-dose arsenic implants, 290
 Continuous liquid-silicon feed, 10
 Critical dimension, 502
 Cross-contamination of dopant impurities, 290
 Crystallographic defects, 309, 312
 Effect on circuit performance, 310
 Crystal pullers, 6, 8, 24
 Cumulative frequency plots, 432

Cylindrical reactor (*see* Barrel reactor)

Czochralski silicon, 5, 24, 39, 50, 333, 370, 460, 469

D

Damage due to laser marking, 65

Deep-level transient spectroscopy (DLTS), 391

Defect generation, 314

Defects in silicon, 161, 162, 389, 400

Defect state spectrum, 241

Denuded zone, 317, 335, 362

Depletion load devices, 414

Device scaling, 230, 260, 408

 Constant field scaling, 230

Dichlorosilane, 181, 207

Digital control mode, 147

Dislocation pinning effect, 314

Dislocations, 312, 317, 322, 370

Distributions, reverse recovery, 379, 381

Dopant incorporation in crystals, 34, 46

Dopants in silicon, 232, 455

Doped poly silicon, 211

 Dopant segregation, 213

 Electrical resistance, 211

 Limitations, 213

 Oxidation rate, 211

Double-crucible crystal growth, 34, 326

Double-layer resists, 92

Dynamic RAMS, 190, 238, 347

E

Education considerations in semiconductor industry, 549

Effect of

 Crystallographic defects on circuit performance, 310

 Ion implant dose and energy on ellipsiometric measurements, 519

 Phase shift on reflectance, 478

 Wafer cleanliness on device, 355

 White-light excitation, 453

Electrical breakdown in thin oxides, 262

Electrically active defects, 163

Electron and hole trapping in oxide, 262, 265

Electron-beam lithography, 86, 102

Electron diffraction, 248

Electron mobility versus doping in silicon, 415

Ellipsiometric measurements, 277, 509, 513

Enhanced short-channel effects, 230

Enhanced vacancy generation, 303

Enhancement transistor, 230

Epi spikes, 72

Epitaxial layer

 For MOS devices, 169, 190, 198

 Lifetime, 398

 Reflectance spectra, 426

 Regrowth, 233

 Resistivity, 149

 Thickness, 149, 160, 477

 Effect of doping, 477

Epitaxial reactor, 147, 151, 174

 Computer-controlled, 175

Equivalue contour maps, 428

Etching properties of polyimide films, 229

Exposure dose dependence, 130

Exposure systems, 89, 96, 129

 Optical mirror systems, 97

Extrinsic gettering, 350

F

Facets in crystals, 27

Field emission SEM, 501

Fish-eye effect, 280
 Fixed charge and interface trap density, 269
 Flatband voltage shift, 267
 Float-zone process, 10, 50, 333, 460
 Critical generator parameters, 52
 Effect of frequency, 50, 58
 Fourier transform infrared spectrometer (FTIR), 448, 459, 469
 Low-temperature measurements, 455

G

Gettering techniques, 16, 312, 385
 Extrinsic gettering, backside damage
 Abrasive blasting, 16
 Direct surface abrasion, 16
 HCl gettering, 394
 Laser beam, 16
 Liquid honing, 16
 Internal gettering, 315, 334
 Intrinsic gettering, 469
 POCl₃ gettering, 469
 Groove-and-stain measurements, 177

H

Halftone maps, 425
 Hall mobility, 224
 HCl etching, 180
 HCl gettering, 394
 High-energy electron penetration, 501
 High-pressure oxidation, 238
 Charges and stress in oxide, 242, 243
 Defect state spectrum, 241
 Impurities in oxide, 240
 Oxidation-induced stacking faults (OSF), 339
 High-temperature annealing, 315
 Horizontal epi reactor, 148, 181

Hot-electron phenomenon, 192-198
 A-c transient determination, 192
 Collection efficiency, 198
 Continuum model, 192
 Resistor mesh substrate model, 197
 Hydrogen distribution in oxide, 252
 Hydrophilic and hydrophobic surfaces, 356

I

Image positioning, 96
 Image quality, 109
 Implanted oxides, 512, 514
 Impurities in oxides, 240
 Induction heating, 149
 Infrared absorption measurements, 317, 373
 Infrared excitation spectrum, 445
 Effect of white-light excitation, 453
 Infrared reflectance measurements, 478
 Infrared transmission, 31, 39
 Interferometric measurements, 478
 Effect of phase shift on reflectance, 478
 Intermetallic dielectrics, 273
 Interstitial diffusion process, 300
 Intrinsic gettering, 315, 334
 Ion-beam lithography, 86
 Ion implantation, 232, 233, 290, 412, 422
 Beam current distributions, 514
 Effect of accelerating voltage variations, 516
 Measurement of dose, 512
 Mechanical scanning, 510, 531
 IR absorption, 470

K

Kinetics of polyimide film deposition, 276

L

Large-diameter crystals, 25
 Large-diameter wafers, 422, 446
 Laser irradiation backside damage, 350
 Laser masking, 17, 62
 Alphanumeric, 63
 Cleanliness requirements, 64, 65
 Effects on further processing, 63, 72, 78
 Damage due to, 65
 Dot-matrix marking, 65
 Legislative requirement for semiconductor industry, 549
 Lifetime, 372, 389
 Deep-level transient spectroscopy, 391
 Effect of cleaning, 392
 Effect of high-temperature processing, 393
 In epitaxial layers, 398
 Photoconductive decay (PCD), 390
 Linewidth control, 108
 Lithographic performance, 117, 133, 229
 Lithographic process, 85
 Cost effectiveness, 86
 Development, 134
 Electron-beam lithography, 86, 102
 Ion-beam lithography, 86
 Modulation transfer function, 90
 Optical technique, 87, 88
 Photomasks, 86
 Post-baking, 142
 Post-exposure curing, 139
 Pre-baking, 129
 UV technique, 87, 88
 X-ray lithography, 86
 LOCOS structures, 412
 Low-pressure CVD, 207, 235, 264
 Low-temperature annealing, 363
 Low-temperature spectrometric measurements, 455

M

Magnetic Czochralski growth (MCZ), 9
 Mask aligners, 96
 Mask fabrication, 103
 Material preparation
 Edge profiling, 14
 Etching, 14
 Lapping, 18
 Polishing, 18
 Slicing, 11
 Measurement of
 Carbon and oxygen in silicon, 455, 459, 469
 Critical dimension, 502
 Groove-and-stain thickness, 177
 Implant dose, 512
 Infrared absorption, 317, 373
 Infrared reflectance, 478
 Lifetime, 372, 389
 Line width, 501
 Oxygen distribution, 362
 Mechanical backside damage, 350
 Mechanical scanning in implanters, 510, 531
 Micro-crystalline structure, 210
 Minority carrier injection, 192
 Minority carrier lifetime measurements, 372, 389
 Modulation transfer function, 90
 MOS memories, 369
 MOS technology, 407, 408, 409
 Device scaling, 408
 NMOS technology, 408
 Process modeling, 409
 MOS transistor, space charge region, 311
 Multilayer resists, 123
 MX reticles, 105

N

Negative resist materials, 129
 Neutron activation analysis, 241

NMOS technology, 190, 372, 408
 Degradation due to drift current,
 190
 Noise/cross talk in MOS devices, 190

O

Optical constants in silicon, 483
 Optical microscopy, 375
 Optical mirror systems, 97
 Optical reflectance in implanted silicon, 523
 Organosilanes, 275, 288
 Orientation effects in epi, 175
 Out-diffusion, 152, 160, 168, 187
 Oxidation using HCl, 245, 257
 Activity fields, 256
 Chlorine distributions in oxide, 249
 Hydrogen distributions in oxide,
 252
 Oxygen incorporation, 325
 Oxygen in silicon, 8, 28, 39, 314, 362,
 445, 459, 469
 Oxygen precipitates, 312, 316, 339,
 370
 Oxygen striation, 41

P

Pancake epitaxial reactor, 148
 Passivation of alkali ions, 248
 Pattern definition, 125, 229
 Effect of process variables, 126
 Pattern distortion, 174
 Pattern shift, 174, 176
 Shift ratio, 182
 Pattern washout, 174
 Phase shift on reflectance, 478
 Phosphorus codiffusion with arsenic,
 292
 Phosphorus diffusion, 417
 Phosphorus vacancy pair diffusion,
 300
 Photoconductive decay (PCD) life-
 time, 390

Photoresist adhesion, 288
 Plasma-enhanced CVD, 218
 Plasma reactors, 220
 POCl₃ gettering, 469
 Polycrystalline films, 410
 Polycrystalline silicon, 6, 55, 206
 Bibliography, 215
 Polyimide films, 276
 Etching properties, 279
 Fish-eye effects, 280
 Kinetics, 276
 Polymer precipitates, 129
 Polysilicon gate capacitors, 263
 Polysiloxane layer, 275
 Positive resist materials, 133
 Process-induced defects, 162, 369
 Projection aligners, 97
 PROSIM simulations, 291

R

Radiant heating, 149
 Radiation damage in oxides,
 267
 Ramp I-V technique, 262
 Reactive ion etching, 261
 Recessed structures, 243
 Recombination center, 312
 Reduced-pressure CVD, 206, 209
 Reflectance spectra of epitaxial layers, 486
 Resist
 Characteristics, 117
 Profile, 108
 Aerial image, 111
 Proximity effects, 114
 Wafer topography, 116
 Systems, 91
 Resistivity mapping, 423
 Reticles, 105
 Reverse recovery distributions, 379,
 381
 RF glow discharges, 219
 Rutherford back-scattering, 247

S

- SAMPLE, 108
- Scanned laser systems, 492
- Scanning electron microscopy (SEM), 109, 357, 501
 - Critical dimension measurement, 502
 - Field emission instrumentation, 501
 - High-energy electron penetration, 501
 - Line-width measurement, 501
- Scanning projection systems, 96
- Scanning transmission electron microscopy (STEM), 246
- Secondary ion mass spectroscopy (SIMS), 246, 296, 482
- Semiconductor equipment considerations, 548
- Silane, 162, 207
- Silicon
 - Axial distributions in crystals, 7, 28, 41, 370
 - Defect formation, 7
 - High-resistivity crystals, 10, 51
 - Large-diameter crystals, 25
 - Orientation, 6, 7, 26
 - Silicon crystal growth, 5, 24, 40, 547
 - Automatic diameter control, 7
 - Automation in crystal growth, 11
 - Continuous liquid silicon feed, 10
 - Crystal pullers, 6, 8, 24
 - Czochralski technique, 5, 24, 39, 50, 333, 370, 460, 469
 - Dopant incorporation, 34, 46
 - Double-crucible growth, 34, 326
 - Effect of cooling, 327, 452
 - Effect of solid solubility, 34
 - Facets, 27
 - Float zone, 10, 50, 333, 460
 - Isotherm shapes, 26
 - Magnetic Czochralski, 9
 - Pull rate, 6, 31, 40
 - Reduced pressure growth, 26
 - Residual contamination, 16
 - Segregation coefficient, 46
 - Skin depth, 58
 - Teal and Little technique, 5
 - Silicon dioxide, 209, 222
 - Silicon epitaxy, 147, 151, 174, 223
 - Autodoping, 151, 157, 162, 168, 176
 - Defect considerations, 161
 - Dichlorosilane, 181, 207
 - Effects of
 - Deposition temperature, 154, 162, 174
 - Gas velocity, 157, 176
 - Pressure, 156
 - Substrate surface quality, 161
 - Effects on structures, 163
 - Growth rate effects, 155, 174
 - In situ* etching, 180
 - Out-diffusion, 152, 160, 168, 187
 - Prebake effects, 154, 168
 - Two-temperature process, 165
 - Silicon foundry, 548
 - Silicon nitride, 209, 221
 - Silicon oxide precipitates, 323
 - Silicon tetrachloride, 162, 181, 207
 - Space charge region, MOS devices, 311
 - SPICE simulations, 193, 539
 - Spin-coating process, 127
 - Spreading resistance measurement technique, 182, 296, 362
 - Spatial resolutions, 552
 - Stacking faults, 312, 370
 - Step-and-repeat projection systems, 99
 - Stress-induced dislocations, 243
 - Stress in oxide, 243
 - Subcollector, 152, 159
 - Subisolation diffusion, 152
 - Substitutional diffusion process, 300
 - SUPREM program, 414, 539
 - SUPREM II program, 415
 - Surface defects, 332, 492, 498

Surface induction effect, 117
 Symbolic maps, 425

T

Teal and Little silicon growth technique, 5
 Thermal donors, 315, 353, 362, 370
 Thin epitaxial layers, 477
 Thin gate oxide
 Electrical breakdown, 262
 Electron and hole trapping, 262, 265, 267
 Fixed charge and interface trap density, 269
 Three-dimensional maps, 432
 Threshold voltage shift, 265
 Transmission electron microscopy (TEM), 385
 Tri-level resists, 94
 Two-step annealing, 317, 370

U

Uniformities of implants, 422, 454
 UV lithography, 87, 88

V

Vacancy generation and diffusion, 300
 Enhanced vacancy generation, 303
 Vector maps, 431
 Vertical integration, 548
 Vertical reactor, 148
 VLSI circuits, 1
 Design capabilities, 542
 Manufacturing complexities, 541

W

Wafer inspection, 17, 20, 492
 Wafer scanner system, 496
 Warpage, 323
 Wright etch, 365

X

X-ray
 Diffraction, 175, 209
 Lithography, 86
 Topography, 41, 47